Central™
Semiconductor Corp.

# PROCESS CP316V

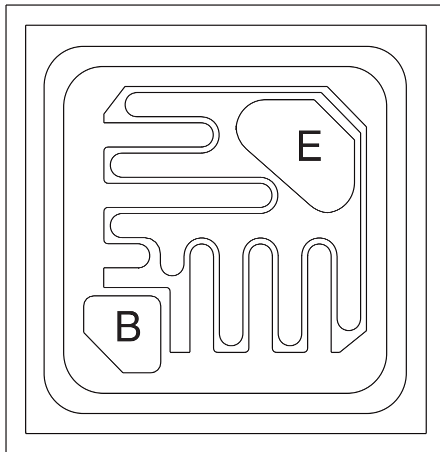
## Small Signal Transistors

### NPN - High Voltage Transistor Chip

**PROCESS DETAILS**

| Process | EPITAXIAL PLANAR |
|---|---|
| Die Size | 20 x 20 MILS |
| Die Thickness | 7.1 MILS |
| Base Bonding Pad Area | 4.0 x 4.0 MILS |
| Emitter Bonding Pad Area | 4.7 x 4.7 MILS |
| Top Side Metalization | Al - 30,000Å |
| Back Side Metalization | Au - 18,000Å |

**GEOMETRY**




BACKSIDE COLLECTOR R0

**GROSS DIE PER 4 INCH WAFER**
29,659

**PRINCIPAL DEVICE TYPES**
CMPT5551
CXT5551
CZT5551
2N5551

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
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R1 (8-October 2008)

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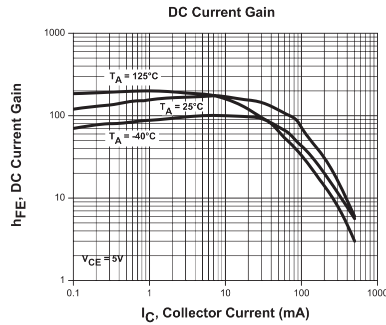
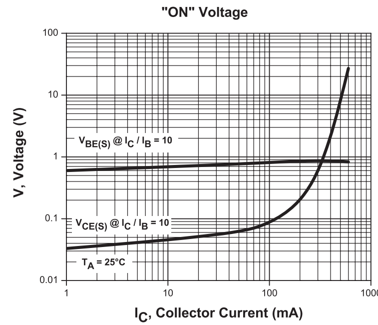
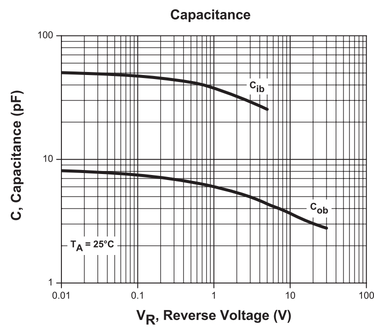
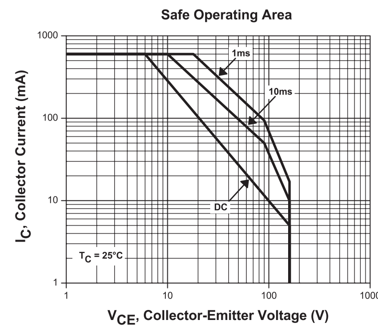
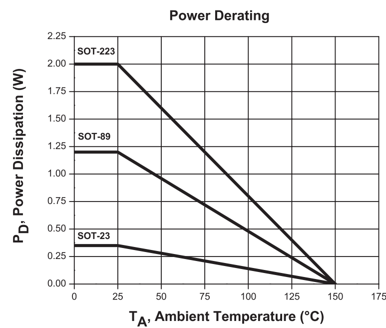
## Typical Electrical Characteristics

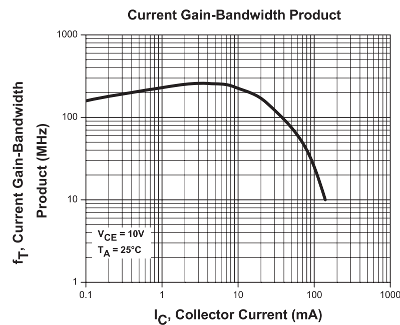
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